

Soon-Ku Hong

List of Publications by Year in descending order

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166
papers

4,449
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117453

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62
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166
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docs citations

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times ranked

4400
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Systematic Investigation of Growth and Properties of Ga ₂ O ₃ Films on C-Plane Sapphire Substrates Prepared by Plasma-Assisted Molecular Beam Epitaxy. ECS Journal of Solid State Science and Technology, 2022, 11, 035008. | 0.9 | 2 |
| 2 | Highly Asymmetric Optical Properties of $\hat{\Gamma}^2$ -Ga ₂ O ₃ as Probed by Linear and Nonlinear Optical Excitation Spectroscopy. Journal of Physical Chemistry C, 2021, 125, 1432-1440. | 1.5 | 16 |
| 3 | Reduction of dislocations in $\hat{\Gamma}^2$ -Ga ₂ O ₃ epilayers grown by halide vapor-phase epitaxy on a conical frustum-patterned sapphire substrate. IUCrj, 2021, 8, 462-467. | 1.0 | 9 |
| 4 | Strengthening and fracture of deformation-processed dual fcc-phase CoCrFeCuNi and CoCrFeCu1.71Ni high entropy alloys. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2020, 781, 139241. | 2.6 | 28 |
| 5 | xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si1.svg"><mml:mrow><mml:mo stretchy="true"></mml:mo><mml:mrow><mml:mover> Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 582 Td (accnt="true"><mml:math> \hat{\Gamma}^2 Ga ₂ O ₃ epilayers grown by halide vapor-phase epitaxy. Journal of Alloys and Compounds, 2020, 834, 155007. | 2.8 | 23 |
| 6 | Nanoscale modulated structures by balanced distribution of atoms and mechanical/structural stabilities in CoCuFeMnNi high entropy alloys. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2019, 762, 138120. | 2.6 | 34 |
| 7 | Effect of in situ annealing on the structural properties of Bi ₂ Te ₃ films grown on (0001) sapphire. Journal of Crystal Growth, 2019, 525, 125191. | 0.7 | 1 |
| 8 | Effects of nanoepitaxial lateral overgrowth on growth of $\hat{\Gamma}^2$ -Ga ₂ O ₃ by halide vapor phase epitaxy. Applied Physics Letters, 2019, 115, . | 1.5 | 17 |
| 9 | Precipitation and decomposition in CoCrFeMnNi high entropy alloy at intermediate temperatures under creep conditions. Materialia, 2019, 8, 100445. | 1.3 | 22 |
| 10 | Growth and characterization of gallium oxide films grown with nitrogen by plasma-assisted molecular-beam epitaxy. Thin Solid Films, 2019, 682, 93-98. | 0.8 | 19 |
| 11 | Growth of single crystal non-polar $\hat{\Gamma}^2$ -Ga ₂ O ₃ on c-plane sapphire substrate. Applied Surface Science, 2019, 481, 819-824. | 3.1 | 10 |
| 12 | Effects of Growth Rate and III/V Ratio on Properties of AlN Films Grown on c-Plane Sapphire Substrates by Plasma-Assisted Molecular Beam Epitaxy. Korean Journal of Materials Research, 2019, 29, 579-585. | 0.1 | 1 |
| 13 | Epitaxial Growth of Bandgap Tunable ZnSn ₂ Films on (0001) Al ₂ O ₃ Substrates by Using a ZnO Buffer. Crystal Growth and Design, 2018, 18, 1385-1393. | 1.4 | 18 |
| 14 | Microstructural Investigation of CoCrFeMnNi High Entropy Alloy Oxynitride Films Prepared by Sputtering Using an Air Gas. Metals and Materials International, 2018, 24, 1285-1292. | 1.8 | 13 |
| 15 | Structural Characterization of CoCrFeMnNi High Entropy Alloy Oxynitride Thin Film Grown by Sputtering. Korean Journal of Materials Research, 2018, 28, 595-600. | 0.1 | 1 |
| 16 | In Situ Oxidation of GaN Layer and Its Effect on Structural Properties of Ga ₂ O ₃ Films Grown by Plasma-Assisted Molecular Beam Epitaxy. Journal of Electronic Materials, 2017, 46, 3499-3506. | 1.0 | 5 |
| 17 | Depth dependent strain analysis in GaN-based light emitting diodes using surface-plasmon enhanced Raman spectroscopy. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600805. | 0.8 | 4 |
| 18 | Simultaneous determination of defect distributions and energies near InGaN/GaN quantum wells by capacitance-voltage measurement. Journal Physics D: Applied Physics, 2017, 50, 39LT03. | 1.3 | 1 |

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|----|---|-----|-----------|
| 19 | Thermally activated deformation and the rate controlling mechanism in CoCrFeMnNi high entropy alloy. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2017, 682, 569-576. | 2.6 | 96 |
| 20 | High Temperature Behavior of Injection and Radiative Efficiencies and Its Effects on the Efficiency Droop in InGaN/GaN Light Emitting Diodes. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 11640-11644. | 0.9 | 2 |
| 21 | A Hydrogen Sulfide Gas Sensor Based on Pd-Decorated ZnO Nanorods. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 10351-10355. | 0.9 | 17 |
| 22 | Effects of growth pressure on morphology of ZnO nanostructures by chemical vapor transport. <i>Chemical Physics Letters</i> , 2016, 658, 182-187. | 1.2 | 12 |
| 23 | Strain mapping in a nanoscale-triangular SiGe pattern by dark-field electron holography with medium magnification mode. <i>Microscopy (Oxford, England)</i> , 2016, 65, 499-507. | 0.7 | 2 |
| 24 | Three-Dimensional Hierarchical Structures of TiO ₂ /CdS Branched Core-Shell Nanorods as a High-Performance Photoelectrochemical Cell Electrode for Hydrogen Production. <i>Journal of the Electrochemical Society</i> , 2016, 163, H434-H439. | 1.3 | 20 |
| 25 | Co ₃ O ₄ @SWCNT composites for H ₂ S gas sensor application. <i>Sensors and Actuators B: Chemical</i> , 2016, 222, 166-172. | 4.0 | 75 |
| 26 | Comprehensive Study of the Surface Morphology Evolution Induced by Thermal Annealing in c-Plane ZnO Films on r-Plane Al ₂ O ₃ Substrates. <i>Science of Advanced Materials</i> , 2016, 8, 358-362. | 0.1 | 2 |
| 27 | Characterization of Basal Plane Dislocations in PVT-Grown SiC by Transmission Electron Microscopy. <i>Korean Journal of Materials Research</i> , 2016, 26, 656-661. | 0.1 | 0 |
| 28 | Fabrication and Photoelectrochemical Properties of a Cu ₂ O/CuO Heterojunction Photoelectrode for Hydrogen Production from Solar Water Splitting. <i>Korean Journal of Materials Research</i> , 2016, 26, 604-610. | 0.1 | 3 |
| 29 | 2D strain measurement in sub-10Ånm SiGe layer with dark-field electron holography. <i>Current Applied Physics</i> , 2015, 15, 1529-1533. | 1.1 | 1 |
| 30 | Effect of indium concentration on morphology of ZnO nanostructures grown by using CVD method and their application for H ₂ gas sensing. <i>Superlattices and Microstructures</i> , 2015, 82, 349-356. | 1.4 | 13 |
| 31 | Photoelectrochemical water splitting properties of hydrothermally-grown ZnO nanorods with controlled diameters. <i>Electronic Materials Letters</i> , 2015, 11, 65-72. | 1.0 | 26 |
| 32 | Investigation of the photoelectrochemical properties for typical ZnO nanostructures grown by using chemical vapor transport. <i>Journal of the Korean Physical Society</i> , 2015, 66, 832-838. | 0.3 | 3 |
| 33 | Growth and characterization of Mg Zn ^{1-x} O films grown on r-plane sapphire substrates by plasma-assisted molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , 2015, 623, 1-6. | 2.8 | 4 |
| 34 | Comprehensive Structural Characterization of Commercial Blue Light Emitting Diode by Using High-Angle Annular Dark Filed Scanning Transmission Electron Microscopy and Transmission Electron Microscopy. <i>Korean Journal of Materials Research</i> , 2015, 25, 1-8. | 0.1 | 0 |
| 35 | Crystal orientation variation of nonpolar AlN films with III/V ratio on r-plane sapphire substrates by plasma-assisted molecular beam epitaxy. <i>Electronic Materials Letters</i> , 2014, 10, 1109-1114. | 1.0 | 4 |
| 36 | Experimental verification of effects of barrier dopings on the internal electric fields and the band structure in InGaN/GaN light emitting diodes. <i>Applied Physics Letters</i> , 2014, 104, . | 1.5 | 8 |

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|----|--|------|-----------|
| 37 | Effect of First-Stage Growth Manipulation and Polarity of SiC Substrates on AlN Epilayers Grown Using Plasma-Assisted Molecular Beam Epitaxy. Korean Journal of Materials Research, 2014, 24, 266~270-266~270. | 0.1 | 1 |
| 38 | Growth and structural characterization of InGaN layers with controlled In content prepared by plasma-assisted molecular beam epitaxy. Thin Solid Films, 2013, 546, 42-47. | 0.8 | 2 |
| 39 | Microstructural Characterization of High Indium-Composition In _x Ga _{1-x} N Epilayers Grown on c-Plane Sapphire Substrates. Microscopy and Microanalysis, 2013, 19, 145-148. | 0.2 | 4 |
| 40 | Surface Polarity Effects on the Hydride Vapor Phase Epitaxial Growth of GaN on 6H-SiC with a Chrome Nitride Buffer Layer. Electrochemical and Solid-State Letters, 2012, 15, H148. | 2.2 | 2 |
| 41 | Hydrothermal Synthesis of ZnO Nanorods in the Presence of a Surfactant. Journal of Nanoscience and Nanotechnology, 2012, 12, 1328-1331. | 0.9 | 2 |
| 42 | Well-to-well non-uniformity in InGaN/GaN multiple quantum wells characterized by capacitance-voltage measurement with additional laser illumination. Applied Physics Letters, 2012, 100, . | 1.5 | 31 |
| 43 | Tin Oxide-Carbon Nanotube Composite for NO _x Sensing. Journal of Nanoscience and Nanotechnology, 2012, 12, 1425-1428. | 0.9 | 26 |
| 44 | Lattice Deformation in a-Plane ZnO Films Grown on r-Plane Al ₂ O ₃ Substrates Grown by Plasma-Assisted Molecular-Beam Epitaxy. Applied Physics Express, 2012, 5, 081101. | 1.1 | 6 |
| 45 | Comprehensive Study about the Effect of Heat Treatment on the Electrical Properties of Single-Crystalline ZnO Materials. Applied Physics Express, 2012, 5, 075801. | 1.1 | 3 |
| 46 | Realization of an open space ensemble for nanowires: a strategy for the maximum response in resistive sensors. Journal of Materials Chemistry, 2012, 22, 6716. | 6.7 | 60 |
| 47 | Comprehensive study of the surface morphology evolution induced by thermal annealing in single-crystalline ZnO Films and ZnO bulks. Journal of the Korean Physical Society, 2012, 61, 1732-1736. | 0.3 | 4 |
| 48 | Improvement of Light Extraction Efficiency and Reduction of Leakage Current in GaN-Based LED Via V-Pit Formation. IEEE Photonics Technology Letters, 2012, 24, 449-451. | 1.3 | 25 |
| 49 | Optimization of a zinc oxide urchin-like structure for high-performance gas sensing. Journal of Materials Chemistry, 2012, 22, 1127-1134. | 6.7 | 73 |
| 50 | Selected Peer-Reviewed Articles from the International Union of Materials Research Societies' International Conference on Electronic Materials 2010 (IUMRS-ICEM 2010). Journal of Nanoscience and Nanotechnology, 2012, 12, 1128-1130. | 0.9 | 0 |
| 51 | Transparent Nanoscale Floating Gate Memory Using Self-Assembled Bismuth Nanocrystals in Bi ₂ Mg _{2/3} Nb _{4/3} O ₇ (BMN) Pyrochlore Thin Films Grown at Room Temperature. Advanced Materials, 2012, 24, 3396-3400. | 11.1 | 5 |
| 52 | Heteroepitaxial growth of GaN on various powder compounds (AlN, LaN, TiN, NbN, ZrN, ZrB ₂ , VN, BeO) by hydride vapor phase epitaxy. Electronic Materials Letters, 2012, 8, 135-139. | 1.0 | 5 |
| 53 | Plasma-Assisted Molecular Beam Epitaxy of In _x Ga _{1-x} N Films on C-plane Sapphire Substrates. Korean Journal of Materials Research, 2012, 22, 185-189. | 0.1 | 0 |
| 54 | Growth Characteristics of AlN by Plasma-Assisted Molecular Beam Epitaxy with Different Al Flux. Korean Journal of Materials Research, 2012, 22, 539-544. | 0.1 | 0 |

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|----|--|------|-----------|
| 55 | A simple fabrication method of randomly oriented polycrystalline zinc oxide nanowires and their application to gas sensing. <i>Advances in Natural Sciences: Nanoscience and Nanotechnology</i> , 2011, 2, 015002. | 0.7 | 6 |
| 56 | Growth and optical properties of ZnO nanorods prepared through hydrothermal growth followed by chemical vapor deposition. <i>Journal of Alloys and Compounds</i> , 2011, 509, 5137-5141. | 2.8 | 32 |
| 57 | Polyaniline-chitosan nanocomposite: High performance hydrogen sensor from new principle. <i>Sensors and Actuators B: Chemical</i> , 2011, 160, 1020-1025. | 4.0 | 40 |
| 58 | Raman and emission characteristics of a-plane InGaN/GaN blue-green light emitting diodes on r-sapphire substrates. <i>Journal of Applied Physics</i> , 2011, 109, 043103-043103-4. | 1.1 | 10 |
| 59 | Suppression of composition modulation in In-rich In _x Ga _{1-x} N layer with high In content ($x \approx 0.67$). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011, 208, 2737-2740. | 0.8 | 0 |
| 60 | Enhanced Photoelectrochemical Activity of the TiO ₂ /ITO Nanocomposites Grown onto Single-Walled Carbon Nanotubes at a Low Temperature by Nanocluster Deposition. <i>Advanced Materials</i> , 2011, 23, 5557-5562. | 11.1 | 33 |
| 61 | The thermal treatment effects of CrN buffer layer on crystal quality of Zn-polar ZnO films. <i>Thin Solid Films</i> , 2011, 519, 3417-3420. | 0.8 | 2 |
| 62 | Properties of (11 $\bar{2}$ 0) a-plane ZnO films on sapphire substrates grown at different temperatures by plasma-assisted molecular beam epitaxy. <i>Thin Solid Films</i> , 2011, 519, 6394-6398. | 0.8 | 15 |
| 63 | Effects of gallium doping on properties of a-plane ZnO films on r-plane sapphire substrates by plasma-assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2011, 29, 03A111. | 0.9 | 3 |
| 64 | Structural Characterization of Bismuth Zinc Oxide Thin Films Grown by Plasma-Assisted Molecular Beam Epitaxy. <i>Korean Journal of Materials Research</i> , 2011, 21, 563-567. | 0.1 | 0 |
| 65 | Growth of Epitaxial AlN Thin Films on Sapphire Substrates by Plasma-Assisted Molecular Beam Epitaxy. <i>Korean Journal of Materials Research</i> , 2011, 21, 634-638. | 0.1 | 2 |
| 66 | Growth and optical properties of ZnO nanorods prepared through hydrothermal growth followed by chemical vapor deposition. , 2010, , . | | 2 |
| 67 | Effects of strain-control layers on piezoelectric field and indium incorporation in InGaN/GaN blue quantum wells. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010, 4, 221-223. | 1.2 | 6 |
| 68 | Interface and defect structures in ZnO films on m-plane sapphire substrates. <i>Journal of Crystal Growth</i> , 2010, 312, 238-244. | 0.7 | 30 |
| 69 | Growth of epitaxial ZnO films on Si (1 1 1) substrates with Cr compound buffer layer by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2010, 312, 2190-2195. | 0.7 | 3 |
| 70 | Investigation of nonpolar (11 $\bar{2}$ 0) a-plane ZnO films grown under various Zn/O ratios by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2010, 312, 2196-2200. | 0.7 | 23 |
| 71 | Investigation of initial growth and very thin () ZnO films by cross-sectional and plan-view transmission electron microscopy. <i>Applied Surface Science</i> , 2010, 256, 1849-1854. | 3.1 | 9 |
| 72 | Microstructural investigation of ZnO films grown on (111) Si substrates by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2010, 312, 1557-1562. | 0.7 | 5 |

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| 73 | Effects of low temperature ZnO and MgO buffer thicknesses on properties of ZnO films grown on (0001) Al ₂ O ₃ substrates by plasma-assisted molecular beam epitaxy. <i>Thin Solid Films</i> , 2010, 519, 223-227. | 0.8 | 12 |
| 74 | Synthesis of porous CuO nanowires and its application to hydrogen detection. <i>Sensors and Actuators B: Chemical</i> , 2010, 146, 266-272. | 4.0 | 142 |
| 75 | Nanocomposite of cobalt oxide nanocrystals and single-walled carbon nanotubes for a gas sensor application. <i>Sensors and Actuators B: Chemical</i> , 2010, 150, 160-166. | 4.0 | 68 |
| 76 | Enhancement of CO gas sensing properties in ZnO thin films deposited on self-assembled Au nanodots. <i>Sensors and Actuators B: Chemical</i> , 2010, 151, 127-132. | 4.0 | 53 |
| 77 | Anisotropic properties of periodically polarity-inverted zinc oxide structures. <i>Journal of Applied Physics</i> , 2010, 107, 123519. | 1.1 | 2 |
| 78 | Investigations on growth and hydrogen gas sensing property of ZnO nanowires prepared by hydrothermal growth. , 2010, , . | | 0 |
| 79 | High-Quality p-Type ZnO Films Grown by Co-Doping of N and Te on Zn-Face ZnO Substrates. <i>Applied Physics Express</i> , 2010, 3, 031103. | 1.1 | 30 |
| 80 | Growth of self-standing GaN substrates. , 2010, , . | | 0 |
| 81 | Effects of Basal Stacking Faults on Electrical Anisotropy of Nonpolar a-Plane (111̄r ₂ O) GaN Light-Emitting Diodes on Sapphire Substrate. <i>IEEE Photonics Technology Letters</i> , 2010, 22, 595-597. | 1.3 | 29 |
| 82 | NO gas sensing properties of ZnO wire-like thin films synthesized by thermal oxidation of sputtered Zn metallic films in air. , 2010, , . | | 0 |
| 83 | Origin of second-order nonlinear optical response of polarity-controlled ZnO films. <i>Applied Physics Letters</i> , 2009, 94, . | 1.5 | 16 |
| 84 | Structural and optical investigations of periodically polarity inverted ZnO heterostructures on (0001) Al ₂ O ₃ . <i>Applied Physics Letters</i> , 2009, 94, 141904. | 1.5 | 10 |
| 85 | Synthesis and hydrogen gas sensing properties of ZnO wirelike thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2009, 27, 1347-1351. | 0.9 | 31 |
| 86 | Spontaneous transition in preferred orientation of GaN domains grown on r-plane sapphire substrate from [112̄A ⁻ 0] to [0001]. <i>Applied Physics Letters</i> , 2009, 94, 102103. | 1.5 | 5 |
| 87 | ZnO nanowires prepared by hydrothermal growth followed by chemical vapor deposition for gas sensors. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 1667-1672. | 1.3 | 20 |
| 88 | Effects of two-step growth by employing Zn-rich and O-rich growth conditions on properties of (1120) ZnO films grown by plasma-assisted molecular beam epitaxy on sapphire. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 1635. | 1.3 | 6 |
| 89 | Lateral arrays of vertical ZnO nanowalls on a periodically polarity-inverted ZnO template. <i>Nanotechnology</i> , 2009, 20, 235304. | 1.3 | 6 |
| 90 | Dynamic Characteristics of Metal-Induced Laterally Crystallized Polycrystalline Silicon Thin-Film Transistor Devices and Circuits Fabricated with Asymmetric Precrystallization. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 020205. | 0.8 | 2 |

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| 91 | Growth and structural properties of ZnO films on (10 \times 10) m-plane sapphire substrates by plasma-assisted molecular beam epitaxy. Journal of Vacuum Science & Technology B, 2009, 27, 1625. | 1.3 | 21 |
| 92 | Ultrastructural observation of electron irradiation damage of lamellar bone. Journal of Materials Science: Materials in Medicine, 2009, 20, 959-965. | 1.7 | 10 |
| 93 | Nanostructural analysis of trabecular bone. Journal of Materials Science: Materials in Medicine, 2009, 20, 1419-1426. | 1.7 | 23 |
| 94 | Electrical and magnetic properties of Mn-doped Si thin films. Physica B: Condensed Matter, 2009, 404, 1686-1688. | 1.3 | 6 |
| 95 | Hydride vapor phase epitaxy of GaN on the vicinal c-sapphire with a CrN interlayer. Journal of Crystal Growth, 2009, 311, 470-473. | 0.7 | 5 |
| 96 | Microstructural Analysis of Void Formation Due to a NH ₄ Cl Layer for Self-Separation of GaN Thick Films. Crystal Growth and Design, 2009, 9, 2877-2880. | 1.4 | 5 |
| 97 | Structural and stimulated emission characteristics of diameter-controlled ZnO nanowires using buffer structure. Journal Physics D: Applied Physics, 2009, 42, 225403. | 1.3 | 5 |
| 98 | Effect of Refined Nitridation of Sapphire Substrates in Hydride Vapor Phase Epitaxy: Definite Correlation of Structural Characteristics between a Low-Temperature-Grown Buffer Layer and a Subsequent High-Temperature-Grown Layer of GaN. Journal of the Korean Physical Society, 2009, 54, 2404-2408. | 0.3 | 0 |
| 99 | Growth of Polarity-Controlled ZnO Films on (0001) Al ₂ O ₃ . Journal of Electronic Materials, 2008, 37, 736-742. | 1.0 | 14 |
| 100 | Strong enhancement of emissions from nanostructured ZnO thin films grown by plasma-assisted molecular beam epitaxy on nanopored Si(001) substrates. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1598-1601. | 0.8 | 0 |
| 101 | The roles of low-temperature buffer layer for thick GaN growth on sapphire. Journal of Crystal Growth, 2008, 310, 920-923. | 0.7 | 7 |
| 102 | Effects of Zn pre-exposure temperature on the microstructures of ZnO films grown on Si(001) substrates by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2008, 310, 1118-1123. | 0.7 | 6 |
| 103 | Characterization of microstructure and defects in epitaxial ZnO films on Al ₂ O ₃ substrates by transmission electron microscopy. Journal of Crystal Growth, 2008, 310, 4102-4109. | 0.7 | 26 |
| 104 | Reduction of dislocations in GaN films on AlN/sapphire templates using CrN nanoislands. Applied Physics Letters, 2008, 92, . | 1.5 | 22 |
| 105 | Anisotropic optical properties of free and bound excitons in highly strained A-plane ZnO investigated with polarized photoreflectance and photoluminescence spectroscopy. Applied Physics Letters, 2008, 92, 201907. | 1.5 | 32 |
| 106 | Growth and structural properties of m-plane ZnO on MgO (001) by molecular beam epitaxy. Applied Physics Letters, 2008, 92, 233505. | 1.5 | 51 |
| 107 | Dynamic Characteristics of Multi-Channel Metal-Induced Unilaterally Precrystallized Polycrystalline Silicon Thin-Film Transistor Devices and Circuits. Korean Journal of Materials Research, 2008, 18, 507-510-507-510. | 0.1 | 2 |
| 108 | Plasma-Assisted Molecular-Beam Epitaxy of ZnO Films on (0001) Al ₂ O ₃ : Effects of the MgO Buffer Layer Thickness. Journal of the Korean Physical Society, 2008, 53, 271-275. | 0.3 | 1 |

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| 109 | Growth and Characterization of Zinc-Oxide Films Grown by Using Plasma-Assisted Molecular Beam Epitaxy on (111) Silicon Substrates with Ti and Titanium Compound Buffer Layers. Journal of the Korean Physical Society, 2008, 53, 276-281. | 0.3 | 8 |
| 110 | Temperature and Polarization Dependence of the Near-Band-Edge Photoluminescence in a Non-Polar ZnO Film Grown by Using Molecular Beam Epitaxy. Journal of the Korean Physical Society, 2008, 53, 288-291. | 0.3 | 3 |
| 111 | Growth and Characterization of Zinc Oxide Nanostructures on (111) Silicon Substrates with Aluminum Compound Layer. Journal of the Korean Physical Society, 2008, 53, 292-298. | 0.3 | 10 |
| 112 | Self-separated freestanding GaN using a NH ₄ Cl interlayer. Applied Physics Letters, 2007, 91, 192108. | 1.5 | 21 |
| 113 | Polarity control of ZnO films on (0001) Al ₂ O ₃ by Cr-compound intermediate layers. Applied Physics Letters, 2007, 90, 201907. | 1.5 | 45 |
| 114 | Structural investigation of nitrated c-sapphire substrate by grazing incidence x-ray diffraction and transmission electron microscopy. Applied Physics Letters, 2007, 91, 202116. | 1.5 | 7 |
| 115 | Structural and optical properties of non-polar A-plane ZnO films grown on R-plane sapphire substrates by plasma-assisted molecular-beam epitaxy. Journal of Crystal Growth, 2007, 309, 121-127. | 0.7 | 90 |
| 116 | Origin of forward leakage current in GaN-based light-emitting devices. Applied Physics Letters, 2006, 89, 132117. | 1.5 | 148 |
| 117 | Slowdown in development of self-assembled InAs ^x GaAs(001) dots near the critical thickness. Journal of Vacuum Science & Technology B, 2006, 24, 1886. | 1.3 | 3 |
| 118 | Control of the ZnO Nanowires Nucleation Site Using Microfluidic Channels. Journal of Physical Chemistry B, 2006, 110, 3856-3859. | 1.2 | 41 |
| 119 | Magnetic and electrical properties of MBE-grown (Ge ^{1-x} Si ^x) ^{1-y} Mn _y thin films. Current Applied Physics, 2006, 6, 478-481. | 1.1 | 11 |
| 120 | Magneto-transport properties of amorphous Ge ^{1-x} Mn _x thin films. Current Applied Physics, 2006, 6, 545-548. | 1.1 | 13 |
| 121 | Growth and magnetism in amorphous Si ^{1-x} Mn _x thin films grown by thermal deposition. Journal of Magnetism and Magnetic Materials, 2006, 304, e167-e169. | 1.0 | 5 |
| 122 | Observation of ferromagnetism and anomalous Hall effect in laser-deposited chromium-doped indium tin oxide films. Solid State Communications, 2006, 137, 41-43. | 0.9 | 44 |
| 123 | Control of crystal polarity in oxide and nitride semiconductors by interface engineering. Journal of Electroceramics, 2006, 17, 255-261. | 0.8 | 8 |
| 124 | The Growth of ZnO on CrN Buffer Layer Using Surface Phase Control by Plasma Assisted Molecular-beam Epitaxy. Materials Research Society Symposia Proceedings, 2006, 957, 1. | 0.1 | 0 |
| 125 | Structural and Optical Properties of ZnO Thin Films Grown on SiO ₂ /Si(100) Substrates by RF Magnetron Sputtering. Korean Journal of Materials Research, 2006, 16, 360-366. | 0.1 | 1 |
| 126 | Nanostructure formation and emission characterization of blue emission InN/GaN quantum well with thin InN well layers. Journal of Crystal Growth, 2005, 281, 349-354. | 0.7 | 14 |

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|-----|--|-----|-----------|
| 127 | Ferromagnetism and anomalous Hall effect in Mn-doped ZnO thin films grown by reactive sputtering. , 2005, , . | | 0 |
| 128 | ZnO epitaxial layers grown on c-sapphire substrate with MgO buffer by plasma-assisted molecular beam epitaxy (P-MBE). Semiconductor Science and Technology, 2005, 20, S13-S21. | 1.0 | 62 |
| 129 | Ferromagnetism and Anomalous Hall Effect in p-Zn _{0.99} Mn _{0.01} O:P. Journal of Magnetism, 2005, 10, 95-98. | 0.2 | 6 |
| 130 | Influence of growth flux and surface supersaturation on InGaAs/GaAs strain relaxation. Applied Physics Letters, 2004, 84, 1085-1087. | 1.5 | 5 |
| 131 | Doping effects in ZnO layers using Li ₃ N as a doping source. Journal of Crystal Growth, 2003, 251, 628-632. | 0.7 | 9 |
| 132 | Study on MgO buffer in ZnO layers grown by plasma-assisted molecular beam epitaxy on Al ₂ O ₃ (0001). Thin Solid Films, 2003, 445, 213-218. | 0.8 | 24 |
| 133 | Nanoheteroepitaxy of GaN on a nanopore array Si surface. Applied Physics Letters, 2003, 83, 1752-1754. | 1.5 | 65 |
| 134 | Correlation of surface chemistry of GaAs substrates with growth mode and stacking fault density in ZnSe epilayers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2002, 20, 1948. | 0.9 | 2 |
| 135 | Control of ZnO film polarity. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1656. | 1.6 | 17 |
| 136 | Control of crystal polarity in a wurtzite crystal: ZnO films grown by plasma-assisted molecular-beam epitaxy on GaN. Physical Review B, 2002, 65, . | 1.1 | 100 |
| 137 | Morphology evolution of ZnO(0001) surface during plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2002, 80, 1358-1360. | 1.5 | 57 |
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